				· · · · · · · · · · · · · · · · · · ·
•	437	((tantalum titanium zirconium niobium) adj oxide or aluminum adj oxide) near4 gate	USPAT;	2003/10/10 11:27
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	0000000000000000
-	5448	channel near3 hot	USPAT;	2003/04/29 14:05
			US-PGPUB;	
			EPO; JPO;	-
			DERWENT;	
			IBM_TDB	
-	9	(channel adj hot) and (tantalum titanium zirconium niobium) adj oxide and aluminum	USPAT;	2003/04/29 14:05
		adj oxide	US-PGPUB	:
-	6271	sram and (floating adj gate non-volatile nonvolatile)	USPAT;	2003/10/10 11:27
			US-PGPUB	
-	157	(conduction adj band adj offset) not ((tunnel adj barrier barrier adj height) near3	USPAT;	2003/04/29 14:06
	1	silicon)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	165	(tunnel adj barrier barrier adj height) near3 silicon	USPAT;	2003/04/29 14:06
			US-PGPUB;	
			EPO; JPO;	
İ			DERWENT,	
1			IBM_TDB	
-	1	work adj function near3 silicon adj dioxide	USPAT;	2003/04/29 14:06
		,	US-PGPUB:	
			EPO; JPO;	
			IBM_TDB	
-	6	((("4271487") or ("4333166") or ("4760556") or ("5042011") or ("5111427") or	USPAT	2003/04/29 14:06
		("5153853") or ("5280205") or ("5399516") or ("5418739") or ("5424569") or		
		("5488587") or ("5497494") or ("5619642") or ("5627785") or ("5796670") or		
	1	("5801401") or ("5852306") or ("5870327") or ("5880991") or ("5986932") or		
	İ	("6009011")).PN.) and sram		
_	40	(((channel adj hot adj electron) and oxide) and tunnel) and high adj dielectric	USPAT;	2003/04/29 14:06
		(((ordinarios da) not da) olocosti, and oxido) and tarmor, and high da) diolocosti	US-PGPUB	2000/04/20 14:00
1.	145	(((floating adj gate) and ((257/315,321).CCLS.)) (((floating adj gate) and 257/3\$2.ccls.)	USPAT;	2003/04/29 14:06
		not ((floating adj gate) and ((257/315,321).CCLS.)))) and (titanium tantalum niobium	US-PGPUB	2000/04/20 14:00
		zirconium aluminum lead) adj oxide	0010100	
-	1	tunnel adj barrier near3 silicon adj dioxide	USPAT;	2003/04/29 14:06
		a management and a morning and	US-PGPUB;	2000/04/20 14:00
			EPO; JPO;	
İ			IBM_TDB	
<u>-</u>	24	(((((floating adj gate) and ((257/315,321).CCLS.)) (((floating adj gate) and 257/3\$2.ccls.)	USPAT;	2003/04/29 14:06
		not ((floating adj gate) and ((257/315,321).CCLS.)))) and (titanium tantalum niobium	US-PGPUB	2000/04/25 14.00
		zirconium aluminum lead) adj oxide) and channel adj hot	30-1 31 00	
_	21	perovskite near3 gate	USPAT;	2003/04/29 14:06
	"	For a series model of gallo	US-PGPUB;	2000/04/23 14:00
			EPO; JPO;	
			DERWENT;	
1			IBM_TDB	
-	6	((sram flip-flop flip adj flop) and (floating adj gate non-volatile nonvolatile)) and	USPAT;	2003/04/29 14:06
		(((tantalum titanium zirconium niobium) adj oxide or aluminum adj oxide) near4 gate)	US-PGPUB;	2003/04/28 14.00
		manual and an an an an an an an an an an an an an	EPO; JPO;	
1			DERWENT;	
			IBM_TDB	
_	135	(sram flip-flop flip adj flop) and (((257/314-317,321,324,390,410,411).CCLS.	USPAT;	2002/40/40 44:20
	155	(365/149,154,185.01,185.08).CCLS.) and @pd>20021203)		2003/10/10 11:20
		(0000/170,104,100.01,100.00).00Lo./ and @pa/20021203)	US-PGPUB;	
			EPO; JPO;	
_	33	(channel adj hot) and (tantalum titanium zirconium niobium) adj oxide	IBM_TDB	2002/04/20 4 4:00
_	33	tonamio auj not) and tantalum tilamum zirconium mobium) auj oxide	USPAT;	2003/04/29 14:06
1.	9	(channel adi hot) and tantalum adi ovide and aluminum adi ovide	US-PGPUB	2002/04/20 44:00
-	]	(channel adj hot) and tantalum adj oxide and aluminum adj oxide	USPAT;	2003/04/29 14:06
	<u> </u>		US-PGPUB	

	609	((conduction adj band adj offset) (((tunnel adj barrier barrier adj height) near3 silicon)	USPAT:	2003/04/29 14:32
	000	and (("5606177").PN.)) (channel adj hot adj electron) ((channel adj hot adj electron)	US-PGPUB;	
1		and oxide) (((channel adj hot adj electron) and oxide) and tunnel) perovskite ((sram	EPO; JPO;	
1		flip-flop flip adj flop) and (floating adj gate non-volatile nonvolatile)) (((sram flip-flop flip	IBM_TDB	
		adj flop) and (floating adj gate non-volatile nonvolatile)) and @pd>20021203) (channel	15.11_155	
		adj hot) (((257/314-317,321,324,390,410,411).CCLS.		
		(365/149,154,185.01,185.08).CCLS.) and @pd>20021203) (((tantalum titanium		
		zirconium niobium) adj oxide or aluminum adj oxide) near4 gate) (channel near3 hot)		
		((channel adj hot) and (tantalum titanium zirconium niobium) adj oxide and aluminum		
		adj oxide) (sram and (floating adj gate non-volatile nonvolatile)) sram (((US-6141248-\$		
	ļ	or US-6069816-\$).did.) and (insulator insulation insulating gate oxide))		
1				,
		((US-6141248-\$).did.) ((conduction adj band adj offset) not ((tunnel adj barrier barrier		
-		adj height) near3 silicon)) (conduction adj band adj offset) (("5606177").PN.)		
		((US-6141248-\$ or US-6069816-\$).did.) ((tunnel adj barrier barrier adj height) near3		
		silicon) "1011" ((((channel adj hot adj electron) and oxide) and tunnel) and high adj		
		dielectric) "1318" (((sram flip-flop flip adj flop) and (floating adj gate non-volatile		
		nonvolatile)) and (((tantalum titanium zirconium niobium) adj oxide or aluminum adj		
		oxide) near4 gate)) ((US-6501677-\$ or US-6501692-\$ or US-6504765-\$ or		
		US-6504775-\$ or US-6504786-\$ or US-6504788-\$ or US-6507124-\$ or US-6509616-\$		
		or US-6510075-\$ or US-6510076-\$ or US-6528817-\$ or US-6528839-\$ or		
		US-6529397-\$ or US-6529399-\$ or US-6529401-\$ or US-6529403-\$ or US-6529407-\$		
		or US-6529408-\$ or US-6531731-\$ or US-6532169-\$ or US-6534819-\$ or US-6535417-\$ or US-6535442-\$ or US-6535453-\$ or US-6538277-\$ or		
		US-6538338-\$).did. or (US-6542401-\$ or US-6545297-\$ or US-6545311-\$ or US-6545905-\$ or US-6549448-\$ or US-6549449-\$ or US-6549450-\$ or US-6549451-\$	İ	
		or US-6549452-\$ or US-6549453-\$ or US-6549458-\$ or US-6512245-\$ or		
		US-6512691-\$ or US-6512700-\$ or US-6512718-\$ or US-6515894-\$ or US-6515931-\$		
		or US-6519176-\$ or US-6519204-\$ or US-6522569-\$ or US-6522582-\$ or		]
		US-6522586-\$ or US-6525382-\$ or US-6525962-\$ or US-6525983-\$ or US-6525985-\$		
		or US-6493255-\$).did. or (US-6493256-\$ or US-6493267-\$ or US-6496887-\$ or US-6501127-\$).did. or (US-20020179960-\$ or US-20020179964-\$ or		ļ
		US-20020180069-\$ or US-20020181273-\$ or US-20020181274-\$ or US-20020185692-\$ or US-20020186579-\$ or US-20020186580-\$ or		
		US-20020186581-\$ or US-20020190343-\$ or US-20020191436-\$ or		
		US-20020195669-\$ or US-20030002328-\$ or US-20030007380-\$ or		
		US-20030007381-\$ or US-20030012049-\$ or US-20030016554-\$ or		
		US-20030021144-\$ or US-20030026124-\$ or US-20030026150-\$ or		
		US-20030021144-\$ or US-20030020124-\$ or US-20030043538-\$ or		
]		US-20030043618-\$ or US-20030052371-\$ or US-20030053330-\$).did. or		
]		(US-20030058687-\$ or US-20030063485-\$ or US-20030063490-\$ or		
		US-20030067043-\$).did.) ((sram flip-flop flip adj flop) and		
		(((257/314-317,321,324,390,410,411).CCLS. (365/149,154,185.01,185.08).CCLS.)		
		and @pd>20021203)) ((channel adj hot) and (tantalum titanium zirconium niobium) adj		
		oxide) ((channel adj hot) and tantalum adj oxide and aluminum adj oxide)) and		
		@pd>20030415		
L		@pa 20000 //O	L	<u> </u>

			·	· · · · · · · · · · · · · · · · · · ·
•	416	(((conduction adj band adj offset) (((tunnel adj barrier barrier adj height) near3 silicon)	USPAT;	2003/04/29 14:25
		and (("5606177").PN.)) (channel adj hot adj electron) ((channel adj hot adj electron)	US-PGPUB;	
		and oxide) (((channel adj hot adj electron) and oxide) and tunnel) perovskite ((sram	EPO; JPO;	
		flip-flop flip adj flop) and (floating adj gate non-volatile nonvolatile)) (((sram flip-flop flip	IBM_TDB	
		adj flop) and (floating adj gate non-volatile nonvolatile)) and @pd>20021203) (channel		
		adj hot) (((257/314-317,321,324,390,410,411).CCLS.		
		(365/149,154,185.01,185.08).CCLS.) and @pd>20021203) (((tantalum titanium		
		zirconium niobium) adj oxide or aluminum adj oxide) near4 gate) (channel near3 hot)		
		((channel adj hot) and (tantalum titanium zirconium niobium) adj oxide and aluminum		
		adj oxide) (sram and (floating adj gate non-volatile nonvolatile)) sram (((US-6141248-\$		
		or US-6069816-\$).did.) and (insulator insulation insulating gate oxide))		
		((US-6141248-\$).did.) ((conduction adj band adj offset) not ((tunnel adj barrier barrier		
[		adj height) near3 silicon)) (conduction adj band adj offset) (("5606177").PN.)		
		((US-6141248-\$ or US-6069816-\$).did.) ((tunnel adj barrier barrier adj height) near3		
		silicon) "1011" ((((channel adj hot adj electron) and oxide) and tunnel) and high adj		
		dielectric) "1318" (((sram flip-flop flip adj flop) and (floating adj gate non-volatile		i
		nonvolatile)) and (((tantalum titanium zirconium niobium) adj oxide or aluminum adj		
1		oxide) near4 gate)) ((US-6501677-\$ or US-6501692-\$ or US-6504765-\$ or		
		US-6504775-\$ or US-6504786-\$ or US-6504788-\$ or US-6507124-\$ or US-6509616-\$		
		or US-6510075-\$ or US-6510076-\$ or US-6528817-\$ or US-6528839-\$ or		
		US-6529397-\$ or US-6529399-\$ or US-6529401-\$ or US-6529403-\$ or US-6529407-\$		
		or US-6529408-\$ or US-6531731-\$ or US-6532169-\$ or US-6534819-\$ or		
		US-6535417-\$ or US-6535442-\$ or US-6535453-\$ or US-6538277-\$ or		
		US-6538338-\$).did. or (US-6542401-\$ or US-6545297-\$ or US-6545311-\$ or		
		US-6545905-\$ or US-6549448-\$ or US-6549449-\$ or US-6549450-\$ or US-6549451-\$		
		or US-6549452-\$ or US-6549453-\$ or US-6549458-\$ or US-6512245-\$ or		
		US-6512691-\$ or US-6512700-\$ or US-6512718-\$ or US-6515894-\$ or US-6515931-\$		
	ł	or US-6519176-\$ or US-6519204-\$ or US-6522569-\$ or US-6522582-\$ or		
		US-6522586-\$ or US-6525382-\$ or US-6525962-\$ or US-6525983-\$ or US-6525985-\$		
		or US-6493255-\$).did. or (US-6493256-\$ or US-6493267-\$ or US-6496887-\$ or		
		US-6501127-\$).did. or (US-20020179960-\$ or US-20020179964-\$ or		
		US-20020180069-\$ or US-20020181273-\$ or US-20020181274-\$ or		
		US-20020185692-\$ or US-20020186579-\$ or US-20020186580-\$ or		
1		US-20020186581-\$ or US-20020190343-\$ or US-20020191436-\$ or		
Ì		US-20020195669-\$ or US-20030002328-\$ or US-20030007380-\$ or		
		US-20030007381-\$ or US-20030012049-\$ or US-20030016554-\$ or	Į	
		US-20030021144-\$ or US-20030026124-\$ or US-20030026150-\$ or		
		US-20030038317-\$ or US-20030042553-\$ or US-20030043538-\$ or		
		US-20030043618-\$ or US-20030052371-\$ or US-20030053330-\$).did. or		
	•	(US-20030058687-\$ or US-20030063485-\$ or US-20030063490-\$ or		
		US-20030067043-\$).did.) ((sram flip-flop flip adj flop) and		
		(((257/314-317,321,324,390,410,411).CCLS. (365/149,154,185.01,185.08).CCLS.)		
	•	and @pd>20021203)) ((channel adj hot) and (tantalum titanium zirconium niobium) adj		
		oxide) ((channel adj hot) and tantalum adj oxide and aluminum adj oxide)) and		i
		@pd>20030415) and @pd>20030418		
1.	40	(((257/314-317,321,324,390,410,411).CCLS. (365/149,154,185.01,185.08).CCLS.)	USPAT;	2003/04/29 14:26
		and @pd>20030415) and @pd>20030418	US-PGPUB:	2000/04/20 14.20
		and wpa- 20000410) and wpa-20000410	EPO; JPO;	
1			IBM_TDB	
1_	117	(sram flip-flop flip adj flop) and (((257/314-317,321,324,390,410,411).CCLS.	USPAT;	2003/10/10 11:21
-	'''	((257/314-317,321,324,380,410,411).CCLS.) (365/149,154,185.01,185.08).CCLS.) and @pd>20030415)	US-PGPUB;	2003/10/10 11.21
		(000) 170,107,100.01,100.00j.00E0.j alia @par20000410j	EPO; JPO;	
}			IBM_TDB	
l <u>.</u>	4202	(257/314-317,321,324,390,410,411).CCLS. (365/149,154,185.01,185.08).CCLS. and	USPAT;	2003/10/10 11:21
-	4202	(207/314-317,321,324,390,410,411).CCLS. (303/149,134,165.01,165.06).CCLS. and @pd>20030415	US-PGPUB	2003/10/10 11.21
<u>-</u>	47	sram and (floating adj gate non-volatile nonvolatile)) and	USPAT;	2003/10/10 11:23
-	"'	(((257/314-317,321,324,390,410,411).CCLS. (365/149,154,185.01,185.08).CCLS. and	US-PGPUB	2003/10/10 11.23
1		(((237/314-317,321,324,390,410,411).CCLS. (303/149,134,183.01,183.06).CCLS. and @pd>20030415) not dram)	UU-FUFUB	
	109	((sram flip-flop flip adj flop) and (((257/314-317,321,324,390,410,411).CCLS.	USPAT;	2003/10/10 11:23
1	109	((365/149,154,185.01,185.08).CCLS.) and @pd>20030415)) not ((sram and (floating	US-PGPUB	2003/10/10 11.23
	1	adj gate non-volatile nonvolatile)) and (((257/314-317,321,324,390,410,411).CCLS.	JOSE GEOD	
		(365/149,154,185.01,185.08).CCLS. and @pd>20030415) not dram))		
L		1 1000/170, 107, 100.01, 100.00/.00E0. and wpur20000410/ not drainly	l	L

-	156	((sram flip-flop flip adj flop) and (((257/314-317,321,324,390,410,411).CCLS.	USPAT;	2003/10/10 11:23
		(365/149,154,185.01,185.08).CCLS.) and @pd>20030415)) ((sram and (floating adj	US-PGPUB	
		gate non-volatile nonvolatile)) and (((257/314-317,321,324,390,410,411).CCLS.	:	
ļ	_	(365/149,154,185.01,185.08).CCLS. and @pd>20030415) not dram))		
-	1530	((sram flip-flop flip adj flop) and (floating adj gate non-volatile nonvolatile)) and	USPAT;	2003/10/10 11:25
		@pd>20030415	US-PGPUB	
-	2008	((conduction adj band adj offset) (((channel adj hot adj electron) and oxide) and	USPAT;	2003/10/10 11:26
	Į.	tunnel) (((sram flip-flop flip adj flop) and (floating adj gate non-volatile nonvolatile)) and	US-PGPUB;	
		@pd>20021203) (channel adj hot) (((tantalum titanium zirconium niobium) adj oxide or	EPO; JPO;	
ł	1	aluminum adj oxide) near4 gate) (channel near3 hot) ((channel adj hot) and (tantalum	IBM_TDB	
İ	1	titanium zirconium niobium) adj oxide and aluminum adj oxide) (sram and (floating adj		
İ	İ	gate non-volatile nonvolatile)) ((conduction adj band adj offset) not ((tunnel adj barrier		
		barrier adj height) near3 silicon)) ((tunnel adj barrier barrier adj height) near3 silicon)		
1	1	((((channel adj hot adj electron) and oxide) and tunnel) and high adj dielectric)		
		((((floating adj gate) and ((257/315,321).CCLS.)) (((floating adj gate) and 257/3\$2.ccls.)		
		not ((floating adj gate) and ((257/315,321).CCLS.)))) and (titanium tantalum niobium		
		zirconium aluminum lead) adj oxide) (perovskite near3 gate) ((sram flip-flop flip adj		
		flop) and (((257/314-317,321,324,390,410,411).CCLS.		
		(365/149,154,185.01,185.08).CCLS.) and @pd>20021203)) ((channel adj hot) and		
		(tantalum titanium zirconium niobium) adj oxide ) ((channel adj hot) and tantalum adj		
		oxide and aluminum adj oxide)) and @pd>20030418		
-	79	sram and ((365/149,154,185.01,185.08).CCLS.) and @pd>20030415	USPAT;	2003/10/10 11:27
		//	US-PGPUB	
-	79	((365/149,154,185.01,185.08).CCLS.) not dram and @pd>20030415	USPAT;	2003/10/10 11:27
			US-PGPUB	
-	28	conduction adj band adj offset and @pd>20030415	USPAT;	2003/10/10 11:27
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	62	((tantalum titanium zirconium niobium) adj oxide or aluminum adj oxide) near4 gate	USPAT;	2003/10/10 11:27
		and @pd>20030415	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	4004	1 (f) - f' f' 1	IBM_TDB	
-	1334	sram and (floating adj gate non-volatile nonvolatile) and @pd>20030415	USPAT;	2003/10/10 11:28
	640	arone with (floating adjugate non-valetile non-valetile) and (floating adjugate	US-PGPUB	2002404044.00
-	612	sram with (floating adj gate non-volatile nonvolatile) and @pd>20030415	USPAT;	2003/10/10 11:29
		oram with amon with (floating adjugate non valetile negregatile) and @nd>20020415	US-PGPUB	2002/40/40 44:20
-	1	sram with cmos with (floating adj gate non-volatile nonvolatile) and @pd>20030415	USPAT;	2003/10/10 11:29
	٠,	conduction adi band adi affact and @nd>20020415	US-PGPUB	2002/40/40 44:20
1	28	conduction adj band adj offset and @pd>20030415	USPAT; US-PGPUB;	2003/10/10 11:30
			EPO; JPO;	
			Derwent;   IBM_tdb	
_	244	perovskite and @pd>20030415	USPAT	2003/10/10 11:30
<u>-</u>	6	(sram flip-flop flip adj flop) and (perovskite and @pd>20030415)	USPAT;	2003/10/10 11:30
-		(state inp-riop inp adjitiop) and (perovisite and (ppd-20030413)	US-PGPUB;	2003/10/10 11.31
			EPO; JPO;	
1			DERWENT;	
	}		IBM_TDB	
	216	(((sram flip-flop flip adj flop) and (((257/314-317,321,324,390,410,411).CCLS.	USPAT;	2003/10/10 12:00
	210	((365/149,154,185.01,185.08).CCLS.) and @pd>20030415)) ((sram and (floating adj	US-PGPUB:	2000/10/10 12:00
		gate non-volatile nonvolatile)) and (((257/314-317,321,324,390,410,411).CCLS.	EPO; JPO;	
		(25/75/14-517,527,534,536,416,417).00E3.	DERWENT;	
		(((365/149,154,185.01,185.08).CCLS.) not dram and @pd>20030415) (sram with	IBM_TDB	
		cmos with (floating adj gate non-volatile nonvolatile) and @pd>20030415) ((sram	IDIW_100	
		flip-flop flip adj flop) and (perovskite and @pd>20030415))		
-	28	floating adj gate with low adj tunnel	USPAT;	2003/10/10 12:01
	[		US-PGPUB;	2000/10/10 12:01
	;		EPO; JPO;	
			DERWENT;	
			IBM_TDB	
			.5100	L

L Number	Hits	Search Text	DB	Time stamp
	775	sram and ((365/149,154,185.01,185.08).CCLS.)	USPAT;	2003/10/10 11:26
			US-PGPUB	
-	2128	((365/149,154,185.01,185.08).CCLS.) not dram	USPAT;	2003/10/10 11:27
			US-PGPUB	
-	70	(sram and (floating adj gate non-volatile nonvolatile)) and	USPAT;	2003/10/10 11:22
		(((365/149,154,185.01,185.08).CCLS.) not dram)	US-PGPUB	
-	7	"4295150"	USPAT	2002/12/04 16:22
-	10641	floating adj gate	USPAT;	2002/12/05 11:55
			US-PGPUB	
-	1187	(floating adj gate) and ((257/315,321).CCLS.)	USPAT;	2002/12/04 18:10
			US-PGPUB	
-	581	(((floating adj gate) and 257/3\$2.ccls.) not ((floating adj gate) and	USPAT;	2002/12/04 18:40
		((257/315,321).CCLS.))) and tunnel	US-PGPUB	
-	47	((257/314-317,321,324,390,410,411).CCLS. (365/149,154,185.01,185.08).CCLS.) and	USPAT;	2003/04/29 14:26
		@pd>20030415	US-PGPUB;	
			EPO; JPO;	
-			IBM_TDB	
-	159	conduction adj band adj offset	USPAT;	2003/10/10 11:30
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	883	channel adj hot adj electron	USPAT;	2003/04/29 14:01
			US-PGPUB	
-	767	(channel adj hot adj electron) and oxide	USPAT;	2003/04/29 14:02
			US-PGPUB	
-	528	((channel adj hot adj electron) and oxide) and tunnel	USPAT;	2003/04/29 14:02
	4.40075	a. a. a. r.a	US-PGPUB	
-	148375	sram flip-flop flip adj flop	USPAT;	2003/10/10 11:30
ļ.			US-PGPUB;	
			EPO; JPO;	
1			DERWENT;	
	124057	Shorting pull gots was valatile namualatile	IBM_TDB	0000/04/00 44:00
-	134957	floating adj gate non-volatile nonvolatile	USPAT;	2003/04/29 14:02
			US-PGPUB;	:
			EPO; JPO; DERWENT;	
			IBM_TDB	
_	282896	work adj function near3 silicon dioxide	USPAT;	2003/04/29 14:03
	202000	work adj furicion flearo silicon dioxide	US-PGPUB;	2003/04/28 14.03
			EPO; JPO;	
			IBM_TDB	
	4296	perovskite	USPAT	2003/10/10 11:30
	9715	(sram flip-flop flip adj flop) and (floating adj gate non-volatile nonvolatile)	USPAT;	2003/04/29 14:03
	0.10	- 1	US-PGPUB;	200007120 14.00
			EPO; JPO;	
			IBM_TDB	
-	1316	((sram flip-flop flip adj flop) and (floating adj gate non-volatile nonvolatile)) and	USPAT;	2003/04/29 14:03
		@pd>20021203	US-PGPUB;	2000,0 1,20 1 1,00
		<b>G</b>	EPO; JPO;	
			IBM_TDB	
-	2025	channel adj hot	USPAT;	2003/04/29 14:04
		•	US-PGPUB;	
1			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	491	((257/314-317,321,324,390,410,411).CCLS. (365/149,154,185.01,185.08).CCLS.) and	USPAT;	2003/04/29 14:04
ŀ		@pd>20021203	US-PGPUB;	
I			EPO; JPO;	
			LEO, JEO.	